

# 4.5 V to 28 V Input, 1.0 A Integrated MOSFET Single Synchronous Buck DC/DC Converter

# BD9E105FP4-Z

## **General Description**

BD9E105FP4-Z is a single synchronous buck DC/DC converter with built-in low on-resistance power MOSFETs. The Light Load Mode control provides excellent efficiency characteristics in light-load conditions, which make the product ideal for equipment, and devices that demand minimal standby power consumption. BD9E105FP4-Z is a current mode control DC/DC converter and features good transient response. It includes internal phase compensation. It achieves the high power density and offers a small footprint on the PCB by employing small package.

## Features

- Single Synchronous Buck DC/DC Converter
- Light Load Mode Control
- Efficiency = 80 %
- (@Iout = 10 mA, VIN = 24 V, Vout = 5 V)
- Internal Phase Compensation
- Over Voltage Protection (OVP)
- Over Current Protection (OCP)
- Short Circuit Protection (SCP)
- Thermal Shutdown Protection (TSD)
- Under Voltage Lockout Protection (UVLO)
- Reduced External Diode
- TSOT23-6L Package

## Applications

- Home Appliance Products (i.e., Air Conditioner, Refrigerator)
- Secondary Power Supply and Adapter Equipment
- Telecommunication Devices

## **Typical Application Circuit**

#### **Key Specifications**

- Input Voltage Range: 4.5 V to 28.0 V Output Voltage Range:  $V_{\text{IN}} x 0.1 \text{ or } 0.7 \text{ V to } V_{\text{IN}} x 0.8 \text{ V}$ Output Current: 1 A (Max) Switching Frequency: 500 kHz (Typ) High Side FET ON Resistance: 165 mΩ (Typ) 95 mΩ (Typ) Low Side FET ON Resistance:
- Shutdown Current:
- Operating Quiescent Current:

Package

TSOT23-6L

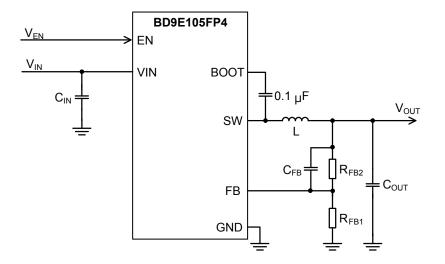
**W (Typ) x D (Typ) x H (Max)** 2.8 mm x 2.92 mm x 0.95 mm

3 µA (Typ)

55 µA (Typ)

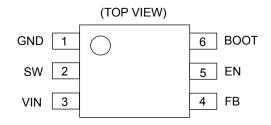


TSOT23-6L



OProduct structure : Silicon integrated circuit OThis product has no designed protection against radioactive rays.

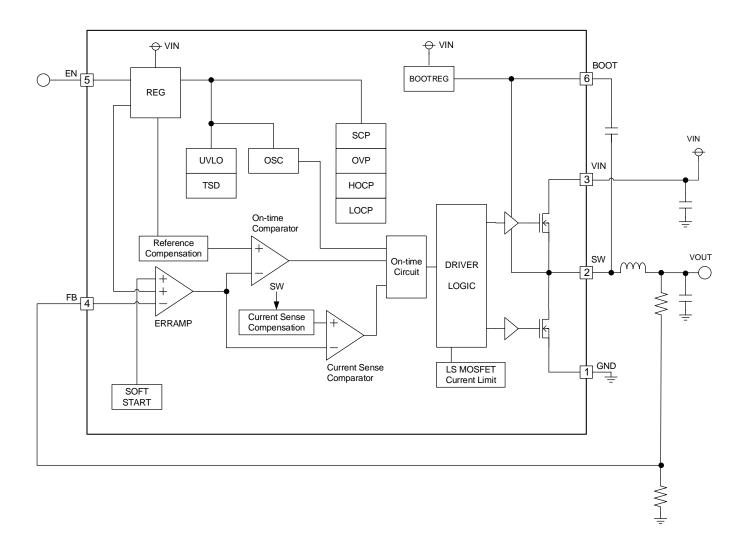
# **Pin Configuration**



# Pin Description

| Pin No. | Pin Name | Function  |
|---------|----------|---|
| 1       | GND      | Ground pins for the control circuit and output stage of the switching regulator.  |
| 2       | SW       | Switch pin. This pin is connected to the source of the High Side FET and the drain of the Low Side FET. Connect a bootstrap capacitor of 0.1 $\mu$ F between this pin and the BOOT pin. In addition, connect an inductor considering the direct current superimposition characteristic. |
| 3       | VIN      | Power supply pin. Connecting 0.1 $\mu$ F (Typ) and 10 $\mu$ F (Typ) ceramic capacitors is recommended. The detail of a selection is described in Selection of Components Externally Connected 1. Input Capacitor.   |
| 4       | FB       | Output voltage feedback pin. See Selection of Components Externally Connected 3. Output Voltage Setting, FB Capacitor for the output voltage setting.   |
| 5       | EN       | Enable pin. The device starts up with setting V <sub>EN</sub> to 1.2 V (Typ) or more. The device enters the shutdown mode with setting V <sub>EN</sub> to 1.1 V (Typ) or less. This pin must be terminated.   |
| 6       | BOOT     | Pin for bootstrap. Connect a bootstrap capacitor of 0.1 $\mu$ F between this pin and the SW pin. The voltage of this pin is the gate drive voltage of the High Side FET.  |

# **Block Diagram**



## **Description of Blocks**

1. REG

This block generates the internal regulator voltage.

2. SOFT START

The Soft Start circuit slows down the rise of output voltage during start-up and controls the current, which allows the prevention of output voltage overshoot and inrush current. The internal soft start time is 5 ms (Typ).

3. ERRAMP

This is the error amplifier. This block compares the FB voltage ( $V_{FB}$ ) and the internal reference voltage. The output voltage is set by the FB external resistors.

4. On-time Comparator

The On-time Comparator compares the Error Amplifier output voltage and the reference voltage compensated by Ontime. When the Error Amplifier output voltage becomes higher than the reference voltage, the output turns low and reports to the On-time Circuit that the output voltage has dropped below the control voltage.

#### 5. On-time Circuit

This block generates the High Side FET on-time signal. Generates an on-time signal determined by the On-time comparator output, OSC signal, and Current Sense Comparator output.

6. Current Sense Comparator

This is a comparator that compares the ERRAMP signal with the current sense signal compensated by ramp signal.

7. UVLO

The UVLO block is for under voltage lockout protection. The device is shutdown when input voltage (V<sub>IN</sub>) falls to 3.9 V (Typ) or less. The threshold voltage has the 350 mV (Typ) hysteresis.

8. TSD

The TSD block is for thermal protection. The device is shutdown when the junction temperature Tj reaches to 175 °C (Typ) or more. The device is automatically restored to normal operation with a hysteresis of 25 °C (Typ) when the Tj goes down.

9. OVP

The OVP block is for over voltage protection. When the FB voltage ( $V_{FB}$ ) exceeds 120 % (Typ) or more of FB threshold voltage  $V_{FBTH}$ , the output MOSFETs are turned off. After  $V_{FB}$  falls 115 % (Typ) or less of  $V_{FBTH}$ , the device is returned to normal operation condition.

#### 10. HOCP

This block is for over current protection of the High Side FET. When the current that flows through the High Side FET reaches the value of over current limit, it turns off the High Side FET and turns on the Low Side FET.

#### 11. LOCP

This block is for over current protection of the Low Side FET. While the current that flows through the Low Side FET over the value of over current limit, the condition that being turned on the Low Side FET is continued.

12. SCP

This block is for short circuit protection. After soft start is completed and in condition where V<sub>FB</sub> is 70 % (Typ) of 0.596 V or less and remained there for 1 ms (Typ), the device is shutdown for 32 ms (Typ) and subsequently initiates a restart.

13. LS MOSFET Current Limit

This circuit is a comparator that monitors the inductor current. When inductor current falls below 0 A (Typ) while the Low Side FET is on, it turns off the Low Side FET.

## 14. DRIVER LOGIC

This block controls the switching operation and protection function operation.

## Absolute Maximum Ratings (Ta = 25 °C)

| Parameter                      | Symbol            | Rating                       | Unit |
|--------------------------------|-------------------|------------------------------|------|
| Input Voltage                  | V <sub>IN</sub>   | -0.3 to +30                  | V    |
| SW Voltage                     | Vsw               | -0.3 to V <sub>IN</sub> +0.3 | V    |
| SW Voltage (10 ns pulse width) | V <sub>SWAC</sub> | -2                           | V    |
| Voltage from GND to BOOT       | VBOOT             | -0.3 to +35                  | V    |
| Voltage from SW to BOOT        | ΔVboot            | -0.3 to +7                   | V    |
| FB Voltage                     | Vfb               | -0.3 to +3                   | V    |
| EN Voltage                     | VEN               | -0.3 to +30                  | V    |
| Output Current                 | I <sub>OUT</sub>  | 1                            | Α    |
| Maximum Junction Temperature   | Tjmax             | 150                          | °C   |
| Storage Temperature Range      | Tstg              | -55 to +150                  | °C   |

Caution 1: Operating the IC over the absolute maximum ratings may damage the IC. The damage can either be a short circuit between pins or an open circuit between pins and the internal circuitry. Therefore, it is important to consider circuit protection measures, such as adding a fuse, in case the IC is operated over the absolute maximum ratings.

Caution 2: Should by any chance the maximum junction temperature rating be exceeded the rise in temperature of the chip may result in deterioration of the properties of the chip. In case of exceeding this absolute maximum rating, design a PCB with thermal resistance taken into consideration by increasing board size and copper area so as not to exceed the maximum junction temperature rating.

#### Thermal Resistance<sup>(Note 1)</sup>

| Parameter  | Symbol          | Thermal Res            | Unit                     |      |
|--|-----------------|------------------------|--------------------------|------|
| Faialletei   | Symbol          | 1s <sup>(Note 3)</sup> | 2s2p <sup>(Note 4)</sup> | Unit |
| TSOT23-6L  |                 |                        |                          |      |
| Junction to Ambient  | θ <sub>JA</sub> | 210.1                  | 99.0                     | °C/W |
| Junction to Top Characterization Parameter <sup>(Note 2)</sup> | $\Psi_{JT}$     | 27.0                   | 22.0                     | °C/W |

(Note 1) Based on JESD51-2A (Still-Air) ,using a BD9E105 Chip.

(Note 2) The thermal characterization parameter to report the difference between junction temperature and the temperature at the top center of the outside surface of the component package. (Note 3) Using a PCB board based on JESD51-3

| (1 | Vote 3) Using a PCB board based or   | i JESD51-3. |                               |
|----|--------------------------------------|-------------|-------------------------------|
|    | Layer Number of<br>Measurement Board | Material    | Board Size                    |
|    | Single                               | FR-4        | 114.3 mm x 76.2 mm x 1.57 mmt |
|    | Тор                                  |             |                               |
|    | Copper Pattern                       | Thickness   |                               |
| Ī  | Footprints and Traces                | 70 µm       |                               |

(Note 4) Using a PCB board based on JESD51-7.

| Layer Number of<br>Measurement Board | Material  | Board Size                   |           |                   |           |
|--------------------------------------|-----------|------------------------------|-----------|-------------------|-----------|
| 4 Layers                             | FR-4      | 114.3 mm x 76.2 mm x 1.6 mmt |           |                   |           |
| Тор                                  |           | 2 Internal Laye              | ers       | Bottom            |           |
| Copper Pattern                       | Thickness | Copper Pattern               | Thickness | Copper Pattern    | Thickness |
| Footprints and Traces                | 70 µm     | 74.2 mm x 74.2 mm            | 35 µm     | 74.2 mm x 74.2 mm | 70 µm     |

## **Recommended Operating Conditions**

| Parameter                                  | Symbol           | Min | Тур | Max     | Unit |
|--|------------------|-----|-----|---------|------|
| Input Voltage                              | V <sub>IN</sub>  | 4.5 | -   | 28.0    | V    |
| Operating Temperature <sup>(Note 1)</sup>  | Topr             | -40 | -   | +85     | °C   |
| Output Current <sup>(Note 1)</sup>         | I <sub>OUT</sub> | 0   | -   | 1       | Α    |
| Output Voltage Setting <sup>(Note 2)</sup> | Vout             | 0.7 | -   | VINX0.8 | V    |

(*Note 1*) Tj must be 150 °C or less under the actual operating environment. Lifetime is derated at junction temperature greater than 125 °C. (*Note 2*) Please use within the range of  $V_{OUT} \ge V_{IN} \times 0.1$  [V].

## Electrical Characteristics (Unless otherwise specified Ta = 25 °C, $V_{IN}$ = 12 V, $V_{EN}$ = 3 V)

| Parameter                             | Symbol             | Min   | Тур   | Max   | Unit | Conditions                                |
|---------------------------------------|--------------------|-------|-------|-------|------|---|
| Input Supply                          | 11                 |       |       |       |      |   |
| Shutdown Current                      | Isdn               | -     | 3     | 15    | μA   | V <sub>EN</sub> = 0 V                     |
| Operating Quiescent Current           | lq                 | -     | 55    | 90    | μA   | I <sub>OUT</sub> = 0 A,<br>No switching   |
| UVLO Threshold Voltage                | V <sub>UVLO1</sub> | 3.7   | 3.9   | 4.1   | V    | V <sub>IN</sub> falling                   |
| UVLO Hysteresis Voltage               | VUVLOHYS           | 300   | 350   | 400   | mV   |   |
| Enable                                |                    |       |       |       |      |   |
| EN Threshold Voltage High             | V <sub>ENH</sub>   | 1.1   | 1.2   | 1.3   | V    | V <sub>EN</sub> rising                    |
| EN Threshold Voltage Low              | VENL               | 1.0   | 1.1   | 1.2   | V    | V <sub>EN</sub> falling                   |
| EN Input Current                      | I <sub>EN</sub>    | -     | 0     | 3     | μA   | V <sub>EN</sub> = 3 V                     |
| Reference Voltage, Error Amplifier,   | Soft Start         |       |       |       |      |   |
| FB Threshold Voltage                  | VFBTH              | 0.587 | 0.596 | 0.605 | V    |   |
| FB Input Current                      | I <sub>FB</sub>    | -     | -     | 100   | nA   | V <sub>FB</sub> = 0.7 V                   |
| Soft Start Time                       | tss                | 3.5   | 5.0   | 6.5   | ms   |   |
| SW (MOSFET)                           |                    |       |       |       |      |   |
| Switching Frequency                   | fsw                | 425   | 500   | 575   | kHz  |   |
| Maximum Duty Ratio                    | D <sub>MAX</sub>   | 80    | -     | -     | %    |   |
| High Side FET ON Resistance           | Ronh               | 82.5  | 165.0 | 247.5 | mΩ   | V <sub>BOOT</sub> - V <sub>SW</sub> = 5 V |
| Low Side FET ON Resistance            | Ronl               | 47.5  | 95.0  | 142.5 | mΩ   |   |
| Protection                            | ·                  |       |       |       |      | ·   |
| High Side Over Current Limit (Note 3) | Іноср              | 1.7   | 2.2   | 2.7   | А    |   |
| Low Side Over Current Limit (Note 3)  | ILOCP              | 1.0   | 1.5   | 2.0   | А    |   |

(Note 3) No tested on outgoing inspection.

## **Typical Performance Curves**

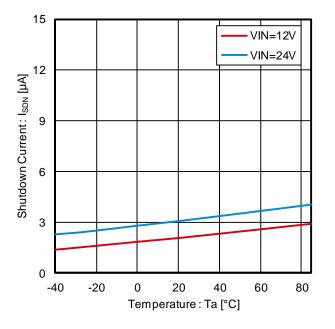


Figure 1. Shutdown Current vs Temperature

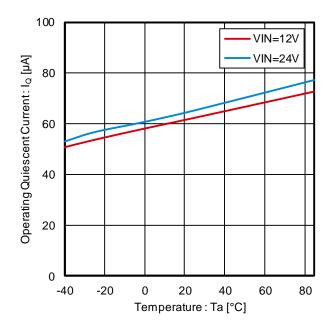


Figure 2. Operating Quiescent Current vs Temperature

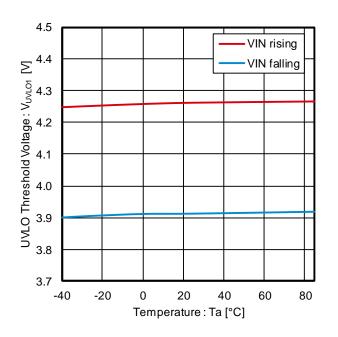


Figure 3. UVLO Threshold Voltage vs Temperature

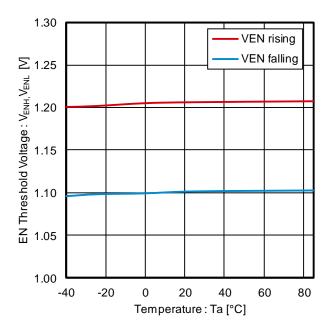


Figure 4. EN Threshold Voltage vs Temperature

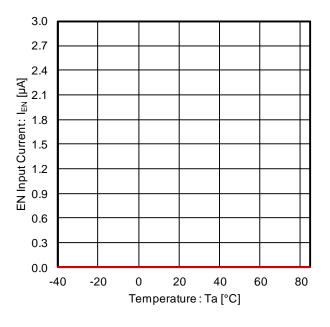


Figure 5. EN Input Current vs Temperature

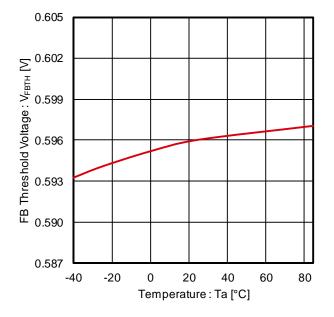


Figure 6. FB Threshold Voltage vs Temperature

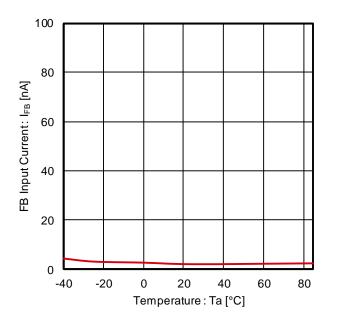


Figure 7. FB Input Current vs Temperature

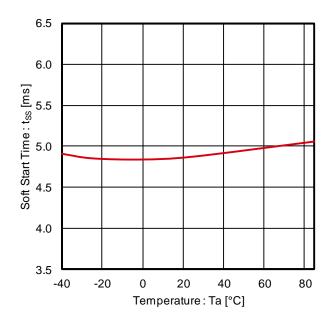


Figure 8. Soft Start Time vs Temperature

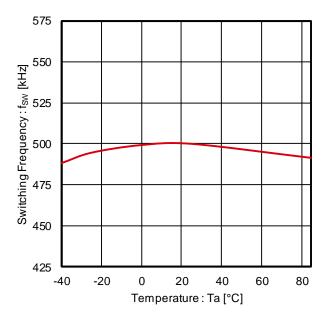
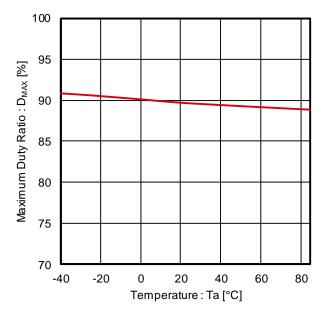
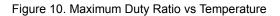


Figure 9. Switching Frequency vs Temperature





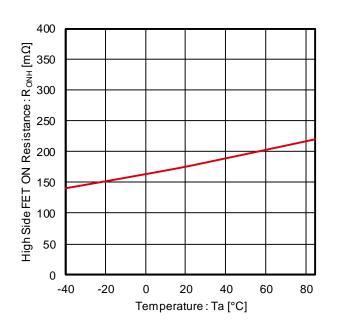


Figure 11. High Side FET ON Resistance vs Temperature

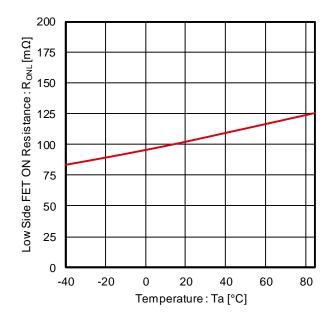


Figure 12. Low Side FET ON Resistance vs Temperature

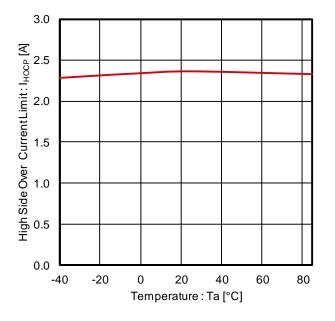


Figure 13. High Side Over Current Limit vs Temperature

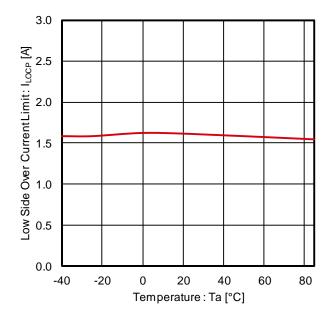


Figure 14. Low Side Over Current Limit vs Temperature

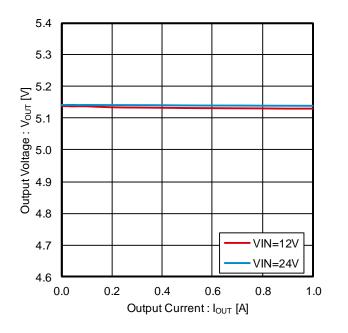


Figure 15. Output Voltage vs Output Current

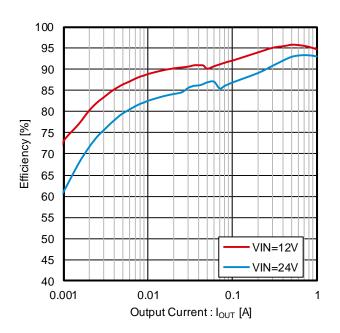


Figure 16. Efficiency vs Output Current

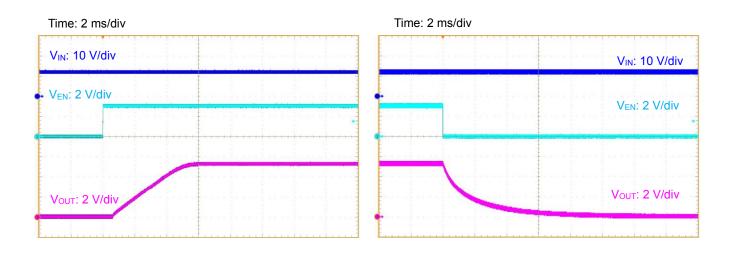


Figure 17. Start-up at No load: V<sub>EN</sub> = 0 V to 3 V  $(V_{IN}$  = 12 V, V<sub>OUT</sub> = 5 V)

Figure 18. Shutdown at No Load V<sub>EN</sub> = 3 V to 0 V  $(V_{IN}$  = 12 V, V<sub>OUT</sub> = 5 V)

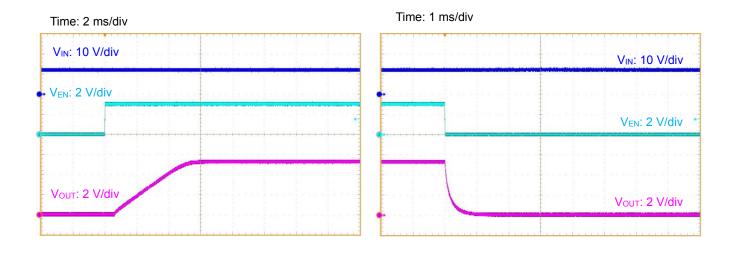


Figure 19. Start-up at  $R_{LOAD}$  = 5  $\Omega$ :  $V_{EN}$  = 0 V to 3 V (V<sub>IN</sub> = 12 V, V<sub>OUT</sub> = 5 V)

Figure 20. Shutdown at  $R_{LOAD}$  = 5  $\Omega$ :  $V_{EN}$  = 3 V to 0 V (V<sub>IN</sub> = 12 V, V<sub>OUT</sub> = 5 V)

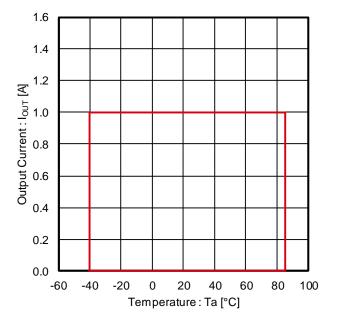


Figure 21. Output Current vs Temperature<sup>(Note 1)</sup> Operating Range: Tj < 150 °C ( $V_{IN}$  = 7 V,  $V_{OUT}$  = 0.7 V)

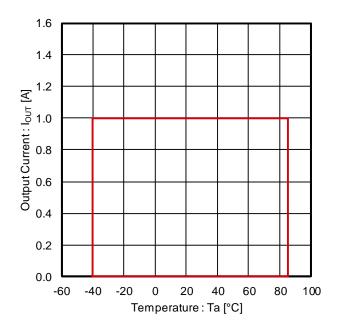
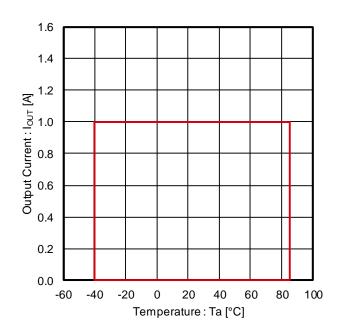
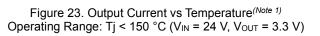
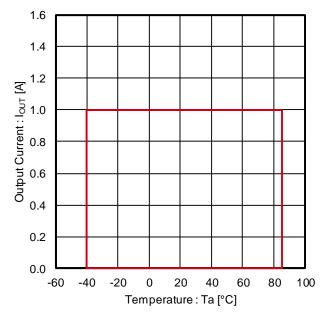
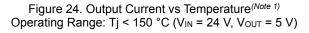


Figure 22. Output Current vs Temperature<sup>(Note 1)</sup> Operating Range: Tj < 150 °C ( $V_{IN}$  = 12 V,  $V_{OUT}$  = 1.2 V)









(Note 1) Measured on FR-4 board 85 mm x 85 mm, Copper Thickness: Top and Bottom 70 µm, 2 Internal Layers 35 µm.

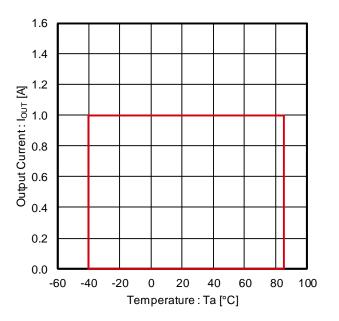


Figure 25. Output Current vs Temperature<sup>(Note 1)</sup> Operating Range: Tj < 150 °C (V<sub>IN</sub> = 24 V, V<sub>OUT</sub> = 12 V)

(Note 1) Measured on FR-4 board 85 mm x 85 mm, Copper Thickness: Top and Bottom 70  $\mu m,$  2 Internal Layers 35  $\mu m.$ 

## **Function Explanation**

### 1. Basic Operation

## (1) DC/DC Converter Operation

BD9E105FP4-Z is a synchronous rectifying step-down switching regulator that achieves faster transient response by employing current mode PWM control system. It utilizes switching operation in PWM (Pulse Width Modulation) mode for heavier load, while it utilizes Light Load Mode control for lighter load to improve efficiency.

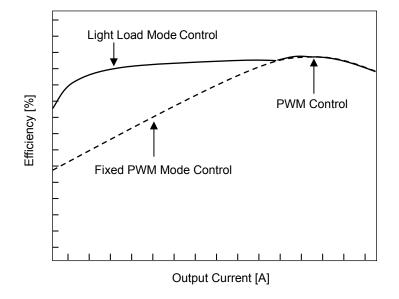


Figure 26. Efficiency Image between Light Load Mode Control and PWM Mode Control

### (2) Enable Control

The startup and shutdown can be controlled by the EN voltage ( $V_{EN}$ ). When  $V_{EN}$  becomes 1.2 V (Typ) or more, the internal circuit is activated and the device starts up. When  $V_{EN}$  becomes 1.1 V (Typ) or less, the device is shutdown. To enable shutdown control with the EN pin, the shutdown interval must be set to 100  $\mu$ s or longer. The startup with  $V_{EN}$  must be at the same time of the input voltage  $V_{IN}$  ( $V_{IN} = V_{EN}$ ) or after supplying  $V_{IN}$ .

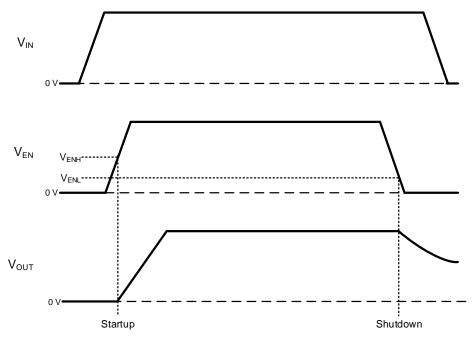
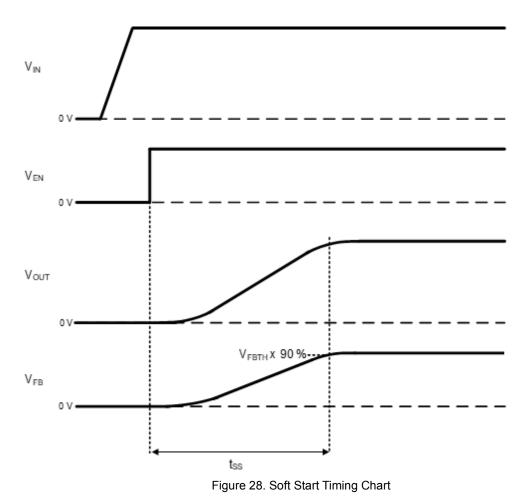


Figure 27. Startup and Shutdown with Enable Control Timing Chart

## 1. Basic Operation – continued

### (3) Soft Start

When  $V_{EN}$  goes high, soft start function operates and output voltage gradually rises. This soft start function can prevent overshoot of the output voltage and excessive inrush current. The soft start time t<sub>SS</sub> is 5 ms (Typ).



## **Function Explanation - continued**

#### 2. Protection

The protection circuits are intended for prevention of damage caused by unexpected accidents. Do not use the continuous protection.

#### (1) Over Current Protection (OCP) / Short Circuit Protection (SCP)

Over Current Protection (OCP) restricts the flowing current through the Low Side FET and the High Side FET for every switching period. If the inductor current exceeds the Low Side OCP  $I_{LOCP} = 1.5 \text{ A}$  (Typ) while the Low Side FET is on, the Low Side FET remains on even with FB voltage V<sub>FB</sub> falls to V<sub>FBTH</sub> = 0.596 V (Typ) or less. If the inductor current becomes less than  $I_{LOCP}$ , the High Side FET is able to be turned on. When the inductor current becomes the High Side OCP  $I_{HOCP} = 2.2 \text{ A}$  (Typ) or more, while the High Side FET is on, the High Side FET is turned off. Output voltage may decrease by changing frequency and duty due to the OCP operation.

Short Circuit Protection (SCP) function is a Hiccup mode. When  $V_{FB}$  remains  $V_{FBTH} \times 70$  % or less for 1 ms, the device stops the switching operation for 32 ms. After that, the device restarts. SCP does not operate during the soft start even if the device is in the SCP conditions. Do not exceed the maximum junction temperature (Tjmax = 150 °C) during OCP and SCP operation.

| VEN           | V <sub>FB</sub>                  | Start-up            | OCP     | SCP     |
|---------------|----------------------------------|---------------------|---------|---------|
|               | ≤ V <sub>FBTH</sub> х 70 % (Тур) | During Soft Start   | Enable  | Disable |
| ≥ 1.2 V (Typ) | > V <sub>FBTH</sub> x 70 % (Тур) | Complete Coff Start | Enable  | Disable |
|               | ≤ V <sub>FBTH</sub> x 70 % (Тур) | Complete Soft Start | Enable  | Enable  |
| ≤ 1.1 V (Typ) | -                                | Shutdown            | Disable | Disable |



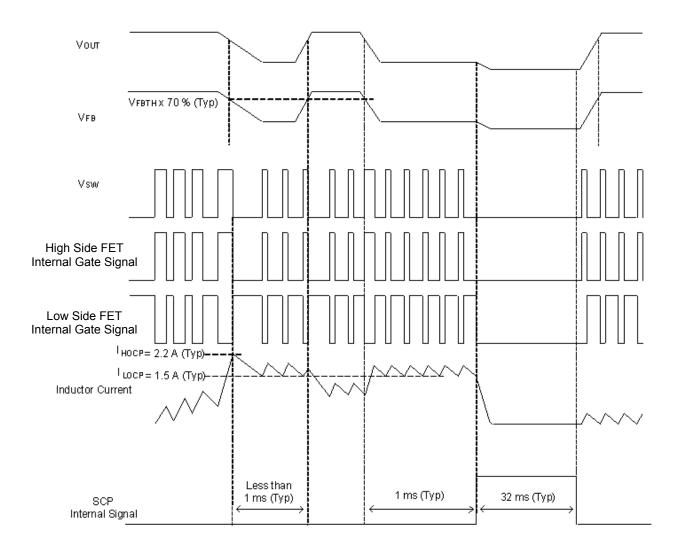
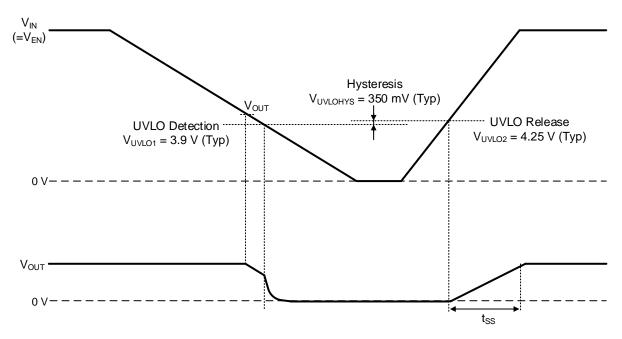


Figure 29. OCP and SCP Timing Chart

#### 2. Protection – continued

### (2) Under Voltage Lockout Protection (UVLO)

When input voltage V<sub>IN</sub> falls to 3.9 V (Typ) or less, the device is shutdown. When V<sub>IN</sub> becomes 4.25 V (Typ) or more, the device starts up. The hysteresis is 350 mV (Typ).





#### (3) Thermal Shutdown Protection (TSD)

Thermal shutdown circuit prevents heat damage to the IC. The device should always operate within the IC's maximum junction temperature rating (Tjmax = 150 °C). However, if it continues exceeding the rating and the junction temperature Tj rises to 175 °C (Typ), the TSD circuit is activated and it turns the output MOSFETs off. When the Tj falls below the TSD threshold, the circuits are automatically restored to normal operation. The TSD threshold has a hysteresis of 25 °C (Typ). Note that the TSD circuit operates in a situation that exceeds the absolute maximum ratings. Therefore, under no circumstances, should the TSD circuit be used in a set design or for any purpose other than protecting the IC from heat damage.

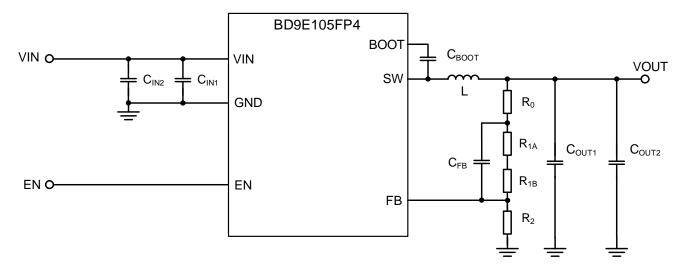
#### (4) Over Voltage Protection (OVP)

When the FB voltage  $V_{FB}$  exceeds  $V_{FBTH} \times 120 \%$  (Typ) or more, the output MOSFETs are turned off to prevent the increase in the output voltage. After the  $V_{FB}$  falls  $V_{FBTH} \times 115 \%$  (Typ) or less, the output MOSFETs are returned to normal operation condition. Switching operation restarts after  $V_{FB}$  falls below  $V_{FBTH}$  (Typ).

## **Application Examples**

### 1. VIN = 5 V to 7 V, VOUT = 0.7 V

| Parameter              | Symbol  | Specification Value |
|------------------------|---------|---------------------|
| Input Voltage          | VIN     | 5 V to 7 V (Typ)    |
| Output Voltage         | Vout    | 0.7 V (Typ)         |
| Maximum Output Current | Ιουτμαχ | 1 A                 |
| Temperature            | Та      | 25 °C               |



#### Figure 31. Application Circuit

| Table 3. Recommended C | Component Values |
|------------------------|------------------|
|------------------------|------------------|

| Part No.                           | Value                     | Part Name          | Size Code<br>(mm) | Manufacturer |
|------------------------------------|---------------------------|--------------------|-------------------|--------------|
| L <sub>1</sub>                     | 3.3 µH                    | CLF7045NIT         | 7470              | TDK          |
| CIN1 <sup>(Note 1)</sup>           | 0.1 µF (50 V, X5R, ±10 %) | GRM155R61H104KE14  | 1005              | Murata       |
| CIN2 <sup>(Note 2)</sup>           | 10 µF (35 V, X5R, ±10 %)  | GRM21BR6YA106KE43L | 2012              | Murata       |
| CBOOT <sup>(Note 3)</sup>          | 0.1 µF (50 V, X5R, ±15 %) | GRM155R61H104KE14  | 1005              | Murata       |
| COUT1 <sup>(Note 4)</sup>          | 47 µF (25 V, X5R, ±20 %)  | TMK325ABJ476MM-P   | 3225              | Yuden        |
| COUT2 <sup>(Note 4)</sup>          | 47 µF (25 V, X5R, ±20 %)  | TMK325ABJ476MM-P   | 3225              | Yuden        |
| Сгв                                | 120 pF (50 V, C0G, ±5 %)  | GRM0335C1H121JA01  | 0603              | Murata       |
| R <sub>0</sub> <sup>(Note 5)</sup> | Short                     | -                  | -                 | -            |
| R <sub>1A</sub>                    | Short                     | -                  | -                 | -            |
| R <sub>1B</sub>                    | 47 kΩ (1 %, 1/16 W)       | MCR01MZPF4702      | 1005              | ROHM         |
| R <sub>2</sub>                     | 270 kΩ (1 %, 1/16 W)      | MCR01MZPF2703      | 1005              | ROHM         |

(Note 1) In order to reduce the influence of high frequency noise, connect a 0.1 µF ceramic capacitor CIN1 as close as possible to the VIN pin and the GND

pin. (Note 2) For the input capacitor C<sub>IN2</sub>, take temperature characteristics, DC bias characteristics, etc. into consideration to set to the actual capacitance of no less than 3.0 μF.

(Note 4) In case of changing the actual capacitance value due to temperature characteristics, DC bias characteristics, etc. of the output capacitor C<sub>OUT1</sub> and

Courz, the loop response characteristics may change. Confirm the actual application. (Note 5) R<sub>0</sub> is an option, used for feedback's frequency response measurement. By inserting a resistor at R<sub>0</sub>, it is possible to measure the frequency response (phase margin) using a FRA. However, the resistor is not used in actual application, use this resistor pattern in short-circuit mode.

<sup>(</sup>Note 3) For the bootstrap capacitor C<sub>BOOT</sub>, take temperature characteristics, DC bias characteristics, etc. into consideration to set to the actual capacitance of no less than 0.022 µF.

## 1. $V_{IN}$ = 5 V to 7 V, $V_{OUT}$ = 0.7 V – continued

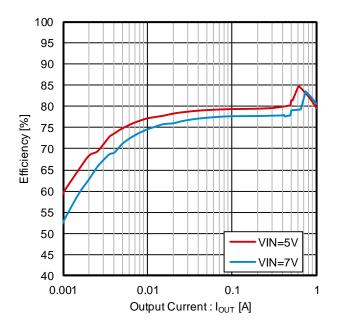


Figure 32. Efficiency vs Output Current

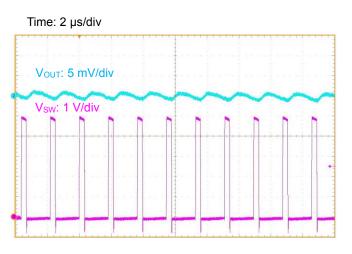


Figure 33. Output Ripple Voltage (VIN = 5 V, IOUT = 1 A)

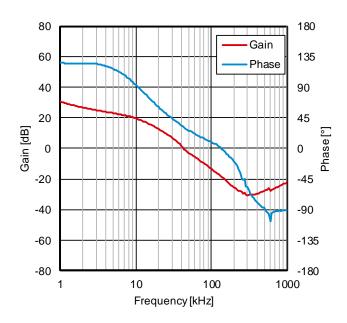
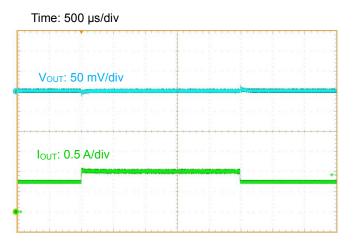
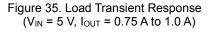


Figure 34. Frequency Characteristics (V<sub>IN</sub> = 5 V, I<sub>OUT</sub> = 1 A)

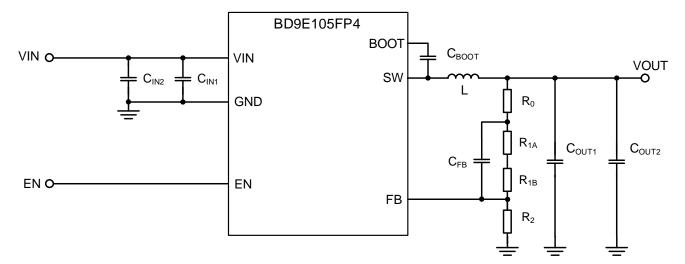




## **Application Examples - continued**

### 2. VIN = 5 V to 7 V, VOUT = 1.2 V

| Parameter              | Symbol  | Specification Value |
|------------------------|---------|---------------------|
| Input Voltage          | VIN     | 5 V to 7 V(Typ)     |
| Output Voltage         | Vout    | 1.2 V (Typ)         |
| Maximum Output Current | Ioutmax | 1 A                 |
| Temperature            | Та      | 25 °C               |



#### Figure 36. Application Circuit

| Table 5. | Recommended | <b>Component Values</b> |
|----------|-------------|-------------------------|
|----------|-------------|-------------------------|

| Part No.                           | Value                     | Part Name          | Size Code<br>(mm) | Manufacturer |
|------------------------------------|---------------------------|--------------------|-------------------|--------------|
| L <sub>1</sub>                     | 4.7 μH                    | CLF7045NIT         | 7470              | TDK          |
| CIN1 <sup>(Note 1)</sup>           | 0.1 µF (50 V, X5R, ±10 %) | GRM155R61H104KE14  | 1005              | Murata       |
| CIN2 <sup>(Note 2)</sup>           | 10 µF (35 V, X5R, ±10 %)  | GRM21BR6YA106KE43L | 2012              | Murata       |
| CBOOT <sup>(Note 3)</sup>          | 0.1 µF (50 V, X5R, ±15 %) | GRM155R61H104KE14  | 1005              | Murata       |
| COUT1 <sup>(Note 4)</sup>          | 47 µF (25 V, X5R, ±20 %)  | TMK325ABJ476MM-P   | 3225              | Yuden        |
| COUT2 <sup>(Note 4)</sup>          | 47 µF (25 V, X5R, ±20 %)  | TMK325ABJ476MM-P   | 3225              | Yuden        |
| Сғв                                | 120 pF (50 V, C0G, ±5 %)  | GRM0335C1H121JA01  | 0603              | Murata       |
| R <sub>0</sub> <sup>(Note 5)</sup> | Short                     | -                  | -                 | -            |
| R <sub>1A</sub>                    | Short                     | -                  | -                 | -            |
| R <sub>1B</sub>                    | 6.2 kΩ (1 %, 1/16 W)      | MCR01MZPF6201      | 1005              | ROHM         |
| R <sub>2</sub>                     | 6.2 kΩ (1 %, 1/16 W)      | MCR01MZPF6201      | 1005              | ROHM         |

(Note 1) In order to reduce the influence of high frequency noise, connect a 0.1 µF ceramic capacitor CIN1 as close as possible to the VIN pin and the GND

pin. (Note 2) For the input capacitor C<sub>IN2</sub>, take temperature characteristics, DC bias characteristics, etc. into consideration to set to the actual capacitance of no less than 3.0 μF.

(Note 4) In case of changing the actual capacitance value due to temperature characteristics, DC bias characteristics, etc. of the output capacitor C<sub>OUT1</sub> and

Courz, the loop response characteristics may change. Confirm the actual application. (Note 5) R<sub>0</sub> is an option, used for feedback's frequency response measurement. By inserting a resistor at R<sub>0</sub>, it is possible to measure the frequency response (phase margin) using a FRA. However, the resistor is not used in actual application, use this resistor pattern in short-circuit mode.

<sup>(</sup>Note 3) For the bootstrap capacitor C<sub>BOOT</sub>, take temperature characteristics, DC bias characteristics, etc. into consideration to set to the actual capacitance of no less than 0.022 µF.

## 2. $V_{IN}$ = 5 V to 7 V, $V_{OUT}$ = 1.2 V – continued

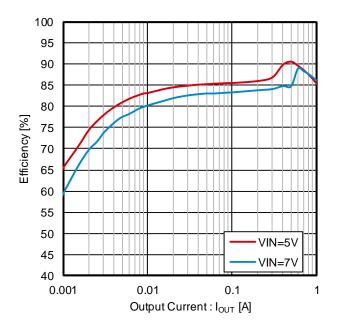


Figure 37. Efficiency vs Output Current

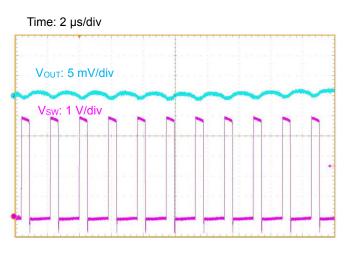


Figure 38. Output Ripple Voltage (VIN = 5 V, IOUT = 1 A)

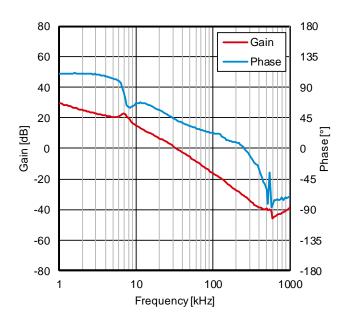


Figure 39. Frequency Characteristics ( $V_{IN}$  = 5 V,  $I_{OUT}$  = 1 A)

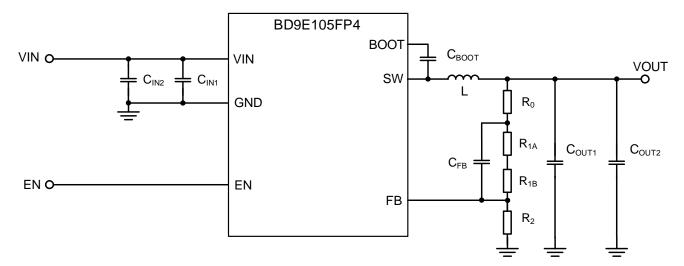
| Time: 500 µs/div                      | <br> | <br>            | <br> |
|---------------------------------------|------|-----------------|------|
| Vout: 100 mV/div                      |      |                 |      |
| · · · · · · · · · · · · · · · · · · · | <br> | <br>            | <br> |
| I <sub>OUT</sub> : 0.5 A/div          |      | - 103 - 204<br> |      |
|                                       |      |                 |      |
|                                       | <br> |                 | <br> |

Figure 40. Load Transient Response ( $V_{IN}$  = 5 V,  $I_{OUT}$  = 0.5 A to 1.0 A)

## **Application Examples - continued**

## 3. VIN = 12 V to 24 V, VOUT = 3.3 V

|                        | Table 6. Specification of Application | n                   |
|------------------------|---------------------------------------|---------------------|
| Parameter              | Symbol                                | Specification Value |
| Input Voltage          | VIN                                   | 12 V to 24 V (Typ)  |
| Output Voltage         | Vout                                  | 3.3 V (Typ)         |
| Maximum Output Current | Ιουτμαχ                               | 1 A                 |
| Temperature            | Та                                    | 25 °C               |



#### Figure 41. Application Circuit

| Table 7. Recommended Component Values | Table 7. | Recommended | <b>Component Values</b> |
|---------------------------------------|----------|-------------|-------------------------|
|---------------------------------------|----------|-------------|-------------------------|

| Part No.                           | Value                     | Part Name          | Size Code<br>(mm) | Manufacturer |
|------------------------------------|---------------------------|--------------------|-------------------|--------------|
| L <sub>1</sub>                     | 10 µH                     | CLF7045NIT         | 7470              | TDK          |
| CIN1 <sup>(Note 1)</sup>           | 0.1 µF (50 V, X5R, ±10 %) | GRM155R61H104KE14  | 1005              | Murata       |
| CIN2 <sup>(Note 2)</sup>           | 10 µF (35 V, X5R, ±10 %)  | GRM21BR6YA106KE43L | 2012              | Murata       |
| CBOOT <sup>(Note 3)</sup>          | 0.1 µF (50 V, X5R, ±15 %) | GRM155R61H104KE14  | 1005              | Murata       |
| COUT1 <sup>(Note 4)</sup>          | 22 µF (25 V, X5R, ±20 %)  | TMK212BBJ226MG-TT  | 2012              | Yuden        |
| COUT2 <sup>(Note 4)</sup>          | 22 µF (25 V, X5R, ±20 %)  | TMK212BBJ226MG-TT  | 2012              | Yuden        |
| Сғв                                | 33 pF (50 V, C0G, ±5 %)   | GRM0335C1H330JA01  | 0603              | Murata       |
| R <sub>0</sub> <sup>(Note 5)</sup> | Short                     | -                  | -                 | -            |
| R <sub>1A</sub>                    | Short                     | -                  | -                 | -            |
| R <sub>1B</sub>                    | 30 kΩ (1 %, 1/16 W)       | MCR01MZPF3002      | 1005              | ROHM         |
| R <sub>2</sub>                     | 6.8 kΩ (1 %, 1/16 W)      | MCR01MZPF6801      | 1005              | ROHM         |

(Note 1) In order to reduce the influence of high frequency noise, connect a 0.1 µF ceramic capacitor CIN1 as close as possible to the VIN pin and the GND

pin. (Note 2) For the input capacitor C<sub>IN2</sub>, take temperature characteristics, DC bias characteristics, etc. into consideration to set to the actual capacitance of no less than 3.0 μF.

(Note 4) In case of changing the actual capacitance value due to temperature characteristics, DC bias characteristics, etc. of the output capacitor C<sub>OUT1</sub> and

Courz, the loop response characteristics may change. Confirm the actual application. (Note 5) R<sub>0</sub> is an option, used for feedback's frequency response measurement. By inserting a resistor at R<sub>0</sub>, it is possible to measure the frequency response (phase margin) using a FRA. However, the resistor is not used in actual application, use this resistor pattern in short-circuit mode.

<sup>(</sup>Note 3) For the bootstrap capacitor C<sub>BOOT</sub>, take temperature characteristics, DC bias characteristics, etc. into consideration to set to the actual capacitance of no less than 0.022 µF.

## 3. $V_{IN}$ = 12 V to 24 V, $V_{OUT}$ = 3.3 V – continued

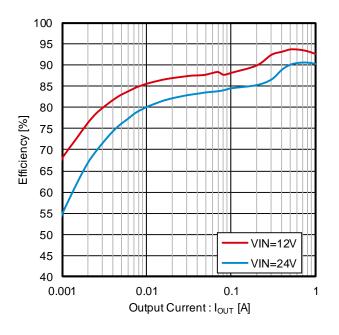


Figure 42. Efficiency vs Output Current

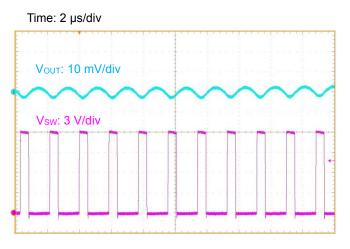


Figure 43. Output Ripple Voltage (VIN = 12 V, IOUT = 1 A)

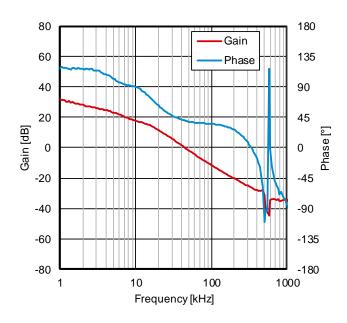


Figure 44. Frequency Characteristics (V<sub>IN</sub> = 12 V, I<sub>OUT</sub> = 1 A)

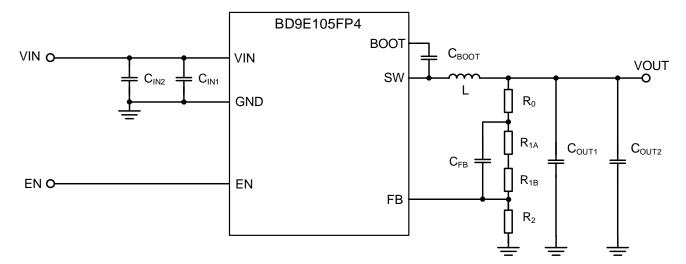
| Time: 500 µs/div             |   | 1 |              | <br> |   |
|------------------------------|---|---|--------------|------|---|
| Vout: 200 mV/div             |   |   |              |      |   |
|                              |   |   | 2<br>        | <br> |   |
| I <sub>OUT</sub> : 0.5 A/div |   |   |              |      |   |
|                              |   |   |              |      |   |
|                              | i | 1 | La constante | <br> | 1 |

Figure 45. Load Transient Response  $(V_{IN} = 12 \text{ V}, I_{OUT} = 0.5 \text{ A to } 1.0 \text{ A})$ 

## **Application Examples - continued**

## 4. VIN = 12 V to 24 V, VOUT = 5 V

| Parameter              | Symbol  | Specification Value |
|------------------------|---------|---------------------|
| Input Voltage          | VIN     | 12 V to 24 V (Typ)  |
| Output Voltage         | Vout    | 5 V (Typ)           |
| Maximum Output Current | Ιουτμαχ | 1 A                 |
| Temperature            | Та      | 25 °C               |



#### Figure 46. Application Circuit

| Table 9. Recommended Component Values | Table 9. | Recommended Component Values |
|---------------------------------------|----------|------------------------------|
|---------------------------------------|----------|------------------------------|

| Part No.                           | Value                     | Part Name          | Size Code<br>(mm) | Manufacturer |
|------------------------------------|---------------------------|--------------------|-------------------|--------------|
| L1                                 | 15 µH                     | CLF7045NIT         | 7470              | TDK          |
| CIN1 <sup>(Note 1)</sup>           | 0.1 µF (50 V, X5R, ±10 %) | GRM155R61H104KE14  | 1005              | Murata       |
| CIN2 <sup>(Note 2)</sup>           | 10 µF (35 V, X5R, ±10 %)  | GRM21BR6YA106KE43L | 2012              | Murata       |
| CBOOT <sup>(Note 3)</sup>          | 0.1 µF (50 V, X5R, ±15 %) | GRM155R61H104KE14  | 1005              | Murata       |
| COUT1 <sup>(Note 4)</sup>          | 22 µF (25 V, X5R, ±20 %)  | TMK212BBJ226MG-TT  | 2012              | Yuden        |
| COUT2 <sup>(Note 4)</sup>          | 22 µF (25 V, X5R, ±20 %)  | TMK212BBJ226MG-TT  | 2012              | Yuden        |
| Сгв                                | 47 pF (50 V, C0G, ±5 %)   | GRM0335C1H470JA01  | 0603              | Murata       |
| R <sub>0</sub> <sup>(Note 5)</sup> | Short                     | -                  | -                 | -            |
| R <sub>1A</sub>                    | Short                     | -                  | -                 | -            |
| R <sub>1B</sub>                    | 56 kΩ (1 %, 1/16 W)       | MCR01MZPF5602      | 1005              | ROHM         |
| R <sub>2</sub>                     | 7.5 kΩ (1 %, 1/16 W)      | MCR01MZPF7501      | 1005              | ROHM         |

(Note 1) In order to reduce the influence of high frequency noise, connect a 0.1 µF ceramic capacitor C<sub>IN1</sub> as close as possible to the VIN pin and the GND

pin. (Note 2) For the input capacitor C<sub>IN2</sub>, take temperature characteristics, DC bias characteristics, etc. into consideration to set to the actual capacitance of no less than 3.0 μF.

(Note 4) In case of changing the actual capacitance value due to temperature characteristics, DC bias characteristics, etc. of the output capacitor C<sub>OUT1</sub> and

Courz, the loop response characteristics may change. Confirm the actual application. (Note 5) R<sub>0</sub> is an option, used for feedback's frequency response measurement. By inserting a resistor at R<sub>0</sub>, it is possible to measure the frequency response (phase margin) using a FRA. However, the resistor is not used in actual application, use this resistor pattern in short-circuit mode.

<sup>(</sup>Note 3) For the bootstrap capacitor C<sub>BOOT</sub>, take temperature characteristics, DC bias characteristics, etc. into consideration to set to the actual capacitance of no less than 0.022 µF.

## 4. $V_{IN}$ = 12 V to 24 V, $V_{OUT}$ = 5 V – continued

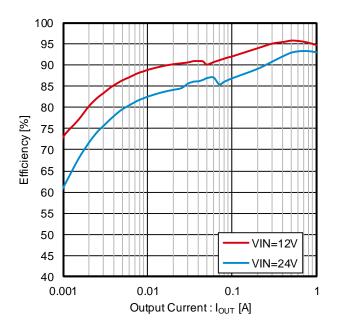


Figure 47. Efficiency vs Output Current

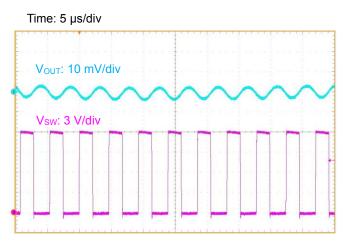


Figure 48. Output Ripple Voltage (VIN = 12 V, IOUT = 1 A)

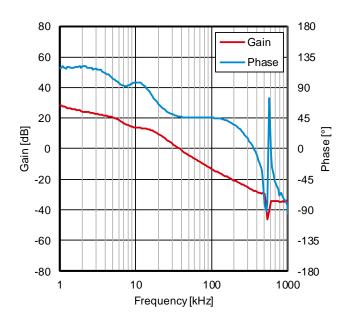


Figure 49. Frequency Characteristics ( $V_{IN}$  = 12 V,  $I_{OUT}$  = 1 A)

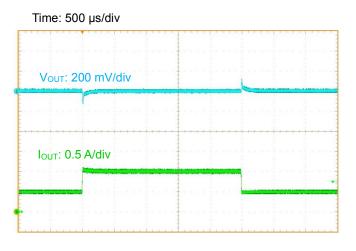
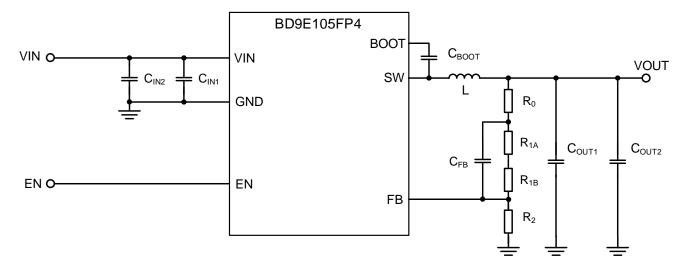


Figure 50. Load Transient Response  $(V_{IN} = 12 \text{ V}, I_{OUT} = 0.5 \text{ A to } 1.0 \text{ A})$ 

## **Application Examples - continued**

## 5. VIN = 24 V, VOUT = 12 V

| Parameter              | Symbol  | Specification Value |
|------------------------|---------|---------------------|
| Input Voltage          | Vin     | 24 V (Typ)          |
| Output Voltage         | Vout    | 12 V (Typ)          |
| Maximum Output Current | Ιουτμαχ | 1 A                 |
| Temperature            | Та      | 25 °C               |



#### Figure 51. Application Circuit

| Table 11. Recommended Component Values |
|--|
|--|

| Part No.                           | Value                     | Part Name          | Size Code<br>(mm) | Manufacturer |
|------------------------------------|---------------------------|--------------------|-------------------|--------------|
| L <sub>1</sub>                     | 22 µH                     | CLF7045NIT         | 7470              | TDK          |
| CIN1 <sup>(Note 1)</sup>           | 0.1 µF (50 V, X5R, ±10 %) | GRM155R61H104KE14  | 1005              | Murata       |
| CIN2 <sup>(Note 2)</sup>           | 10 µF (35 V, X5R, ±10 %)  | GRM21BR6YA106KE43L | 2012              | Murata       |
| CBOOT <sup>(Note 3)</sup>          | 0.1 µF (50 V, X5R, ±15 %) | GRM155R61H104KE14  | 1005              | Murata       |
| COUT1 <sup>(Note 4)</sup>          | 22 µF (25 V, X5R, ±20 %)  | TMK212BBJ226MG-TT  | 2012              | Yuden        |
| COUT2 <sup>(Note 4)</sup>          | 22 µF (25 V, X5R, ±20 %)  | TMK212BBJ226MG-TT  | 2012              | Yuden        |
| Сғв                                | 12 pF (50 V, C0G, ±5 %)   | GRM0335C1H120JA01  | 0603              | Murata       |
| R <sub>0</sub> <sup>(Note 5)</sup> | Short                     | -                  | -                 | -            |
| R <sub>1A</sub>                    | Short                     | -                  | -                 | -            |
| R <sub>1B</sub>                    | 130 kΩ (1 %, 1/16 W)      | MCR01MZPF1303      | 1005              | ROHM         |
| R <sub>2</sub>                     | 6.8 kΩ (1 %, 1/16 W)      | MCR01MZPF6801      | 1005              | ROHM         |

(Note 1) In order to reduce the influence of high frequency noise, connect a 0.1 µF ceramic capacitor CIN1 as close as possible to the VIN pin and the GND

pin. (Note 2) For the input capacitor C<sub>IN2</sub>, take temperature characteristics, DC bias characteristics, etc. into consideration to set to the actual capacitance of no less than 3.0 μF.

(Note 4) In case of changing the actual capacitance value due to temperature characteristics, DC bias characteristics, etc. of the output capacitor C<sub>OUT1</sub> and

Courz, the loop response characteristics may change. Confirm the actual application. (Note 5) R<sub>0</sub> is an option, used for feedback's frequency response measurement. By inserting a resistor at R<sub>0</sub>, it is possible to measure the frequency response (phase margin) using a FRA. However, the resistor is not used in actual application, use this resistor pattern in short-circuit mode.

<sup>(</sup>Note 3) For the bootstrap capacitor C<sub>BOOT</sub>, take temperature characteristics, DC bias characteristics, etc. into consideration to set to the actual capacitance of no less than 0.022 µF.

## 5. $V_{IN}$ = 24 V, $V_{OUT}$ = 12 V – continued

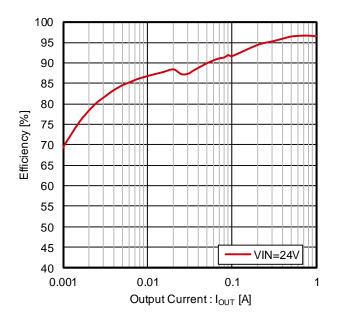


Figure 52. Efficiency vs Output Current

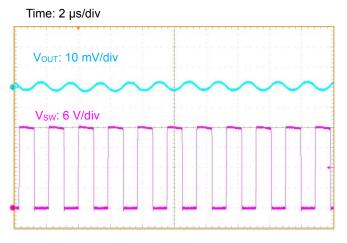
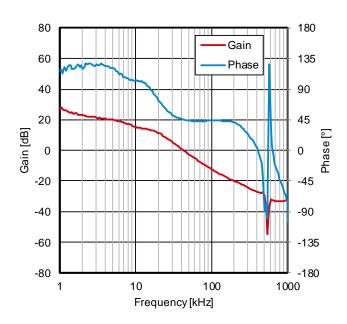
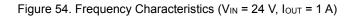


Figure 53. Output Ripple Voltage (VIN = 24 V, IOUT = 1 A)





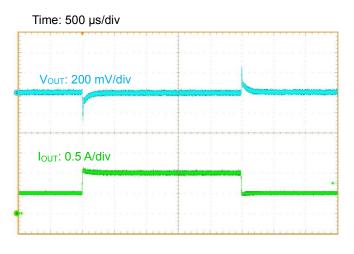


Figure 55. Load Transient Response ( $V_{IN}$  = 24 V,  $I_{OUT}$  = 0.5 A to 1.0 A)

## Selection of Components Externally Connected

Contact us if not use the recommended component values in Application Examples.

#### 1. Input Capacitor

Use ceramic type capacitor for the input capacitor. The input capacitor is used to reduce the input ripple noise and it is effective by being placed as close as possible to the VIN pin. Set the capacitor value so that it does not fall to 3  $\mu$ F considering the capacitor value variances, temperature characteristics, DC bias characteristics, aging characteristics, and etc. The PCB layout and the position of the capacitor may lead to IC malfunction. Refer to the notes on the PCB layout on PCB Layout Design when designing PCB layout. In addition, the capacitor with value 0.1  $\mu$ F can be connected as close as possible to the VIN pin and the GND pin in order to reduce the high frequency noise.

#### 2. Output LC Filter

In order to supply a continuous current to the load, the DC/DC converter requires an LC filter for smoothing the output voltage. For recommended inductance, use the values listed in Table 12.

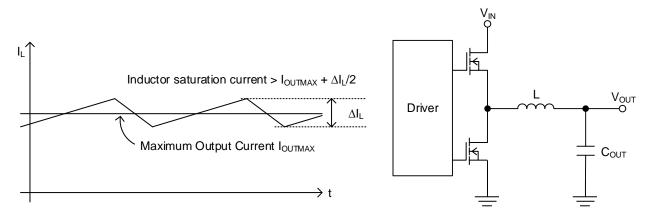
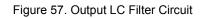


Figure 56. Waveform of Inductor Current



For example, given that  $V_{IN}$  = 12 V,  $V_{OUT}$  = 5 V, L = 15 µH, and the switching frequency  $f_{SW}$  = 500 kHz, Inductor current  $\Delta I_L$  can be represented by the following equation.

$$\Delta I_L = V_{OUT} \times (V_{IN} - V_{OUT}) \times \frac{1}{V_{IN} \times f_{SW} \times L} = 0.389$$
 [A]

The rated current of the inductor (Inductor saturation current) must be larger than the sum of the maximum output current  $I_{OUTMAX}$  and 1/2 of the inductor ripple current  $\Delta I_L$ .

Use ceramic type capacitor for the output capacitor  $C_{OUT}$ . For recommended actual capacitance, use the values listed in Table 12.  $C_{OUT}$  affects the output ripple voltage. Select  $C_{OUT}$  so that it must satisfy the required ripple voltage characteristics.

The output ripple voltage can be estimated by the following equation.

$$\Delta V_{RPL} = \Delta I_L \times \left( R_{ESR} + \frac{1}{8 \times C_{OUT} \times f_{SW}} \right)$$
 [V]

where:

 $R_{ESR}$  is the Equivalent Series Resistance (ESR) of the output capacitor.

For example, given that  $C_{OUT}$  = 44 µF and R<sub>ESR</sub> = 5 m $\Omega$ ,  $\Delta V_{RPL}$  can be calculated as below.

$$\Delta V_{RPL} = 0.389 \, A \times \left(5 \, m\Omega + \frac{1}{8 \times 44 \, \mu F \times 500 \, kHz}\right) = 4.15 \, \text{[mV]}$$

## 2. Output LC Filter – continued

In addition, the total capacitance connected to V<sub>OUT</sub> needs to satisfy the value obtained by the following equation.

$$C_{OUTMAX} < \frac{t_{SSMIN}}{V_{OUT}} \times (I_{OUTMAX} + \frac{\Delta I_L}{2} - I_{OUTSS})$$
 [F]

where:

 $t_{SSMIN} \ \text{is the minimum soft start time.} \\ V_{OUT} \ \text{is the output voltage.} \\ I_{OUTMAX} \ \text{is the maximum output current.} \\ \Delta I_L \ \text{is the inductor ripple current.} \\ I_{OUTSS} \ \text{is the maximum output current during soft start.}$ 

For example, given that  $V_{IN}$  = 12 V,  $V_{OUT}$  = 5.0 V, L = 15  $\mu$ H, fsw = 500 kHz (Typ), tssmin = 3.5 ms, I<sub>OUTMAX</sub> = 1 A, and I<sub>OUTSS</sub> = 1 A, C<sub>OUTMAX</sub> can be calculated as below.

$$C_{OUTMAX} < \frac{3.5 \, ms}{5.0 \, V} \times (1 \, A + \frac{0.389 \, A}{2} - 1 \, A) = 136 \, [\mu F]$$

If the total capacitance connected to V<sub>OUT</sub> is larger than C<sub>OUTMAX</sub>, over current protection may be activated by the inrush current at startup and prevented to turn on the output. Confirm this on the actual application.

| <b>V</b> IN <b>[V]</b> | <b>V</b> out <b>[V]</b> | Inductor L<br>[µH] | Coυτ_EFF <sup>(Note 1)</sup><br>[μ <b>F</b> ] | R <sub>1B</sub> [kΩ] | R₂ [kΩ] | С <sub>FB</sub> [pF] |
|------------------------|-------------------------|--------------------|---|----------------------|---------|----------------------|
| 5                      | 0.7                     | 3.3                | 94  | 47                   | 270     | 120                  |
| 5 to 12                | 1.2                     | 4.7                | 94  | 6.2                  | 6.2     | 120                  |
| 5 to 24                | 3.3                     | 10                 | 44  | 30                   | 6.8     | 33                   |
| 12 to 24               | 5                       | 15                 | 44  | 56                   | 7.5     | 47                   |
| 24                     | 12                      | 22                 | 44  | 130                  | 6.8     | 12                   |

Table 12. Recommended external parts value

(Note 1)  $C_{\text{OUT}\_\text{EFF}}$  is the sum of actual output capacitance.

## Selection of Components Externally Connected – continued

#### 3. Output Voltage Setting, FB Capacitor

The output voltage can be set by the feedback resistance ratio connected to the FB pin. For recommended  $R_{1B}$  and  $R_2$ , use the values listed in Table 12.

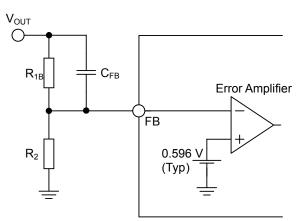


Figure 58. Feedback Resistor Circuit

The output voltage  $V_{\mbox{\scriptsize OUT}}$  can be calculated as below.

$$V_{OUT} = \frac{R_{1B} + R_2}{R_2} \times 0.596$$
 [V]

$$0.7 \leq V_{OUT} \leq (V_{IN} \times 0.8) \text{ [V]}$$

#### 4. Bootstrap Capacitor

The bootstrap capacitor 0.1  $\mu$ F is recommended. Connect the capacitor between the SW pin and the BOOT pin. For the capacitance, take temperature characteristics, DC bias characteristics, and etc. into consideration to set to the actual capacitance of no less than 0.022  $\mu$ F.

## **PCB Layout Design**

PCB layout design for DC/DC converter is very important. Appropriate layout can avoid various problems concerning power supply. Figure 59-a to Figure 59-c show the current path in a buck DC/DC converter. The Loop 1 in Figure 59-a is a current path when H-side switch is ON and L-side switch is OFF, the Loop 2 in Figure 59-b is when H-side switch is OFF and L-side switch is ON. The thick line in Figure 59-c shows the difference between Loop1 and Loop2. The current in thick line change sharply each time the switching element H-side and L-side switch change from OFF to ON, and vice versa. These sharp changes induce a waveform with harmonics in this loop. Therefore, the loop area of thick line that is consisted by input capacitor and IC should be as small as possible to minimize noise. For more details, refer to application note of switching regulator series "PCB Layout Techniques of Buck Converter".

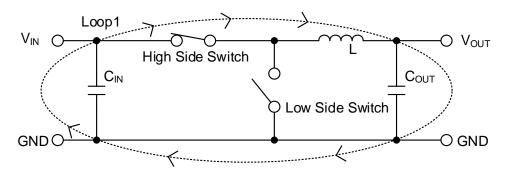


Figure 59-a. Current Path when High Side Switch = ON, Low Side Switch = OFF

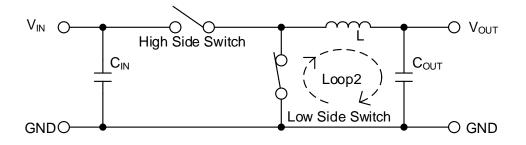


Figure 59-b. Current Path when High Side Switch = OFF, Low Side Switch = ON

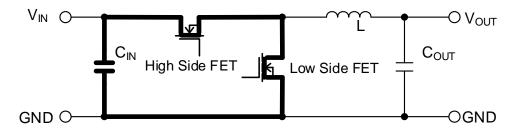
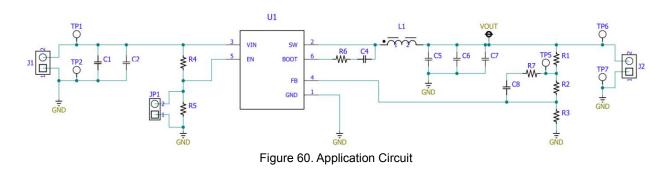


Figure 59-c. Difference of Current and Critical Area in Layout

## PCB Layout Design – continued

When designing the PCB layout, pay attention to the following points:

- Connect the input capacitor C<sub>1</sub> and C<sub>2</sub> as close as possible to the VIN pin and the GND pin on the same plane as the IC.
- Switching nodes such as SW are susceptible to noise due to AC coupling with other nodes. Route the inductor pattern L as thick and as short as possible.
- The feedback line connected to the FB pin should be as far away from the SW nodes as possible.
- Place the output capacitor  $C_5$ ,  $C_6$  and  $C_7$  away from input capacitor  $C_1$  and  $C_2$  to avoid harmonics noise from the input.
- R1 is provided for the measurement of feedback frequency characteristics (optional). By inserting a resistor into R1, it
  is possible to measure the frequency characteristics of feedback (phase margin) using FRA etc. R1 is short-circuited
  for normal use.



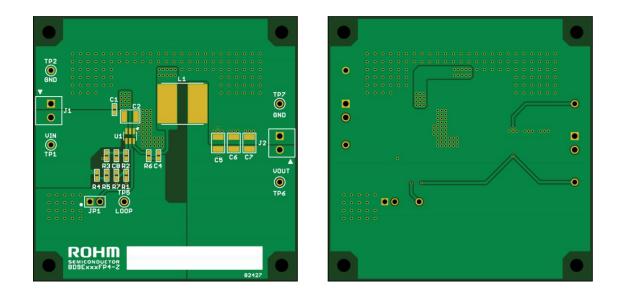
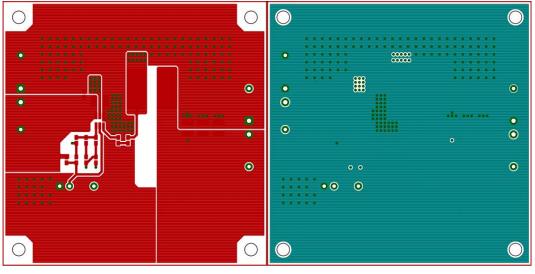


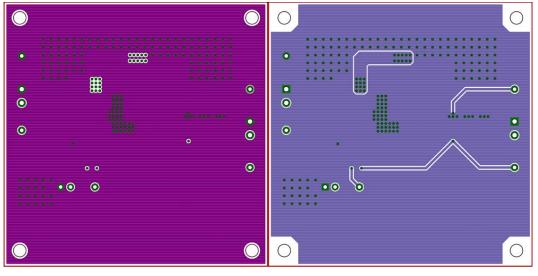
Figure 61. Example of PCB Layout (Silkscreen Overlay)

## PCB Layout Design – continued



Top Layer

Inner 1 Layer

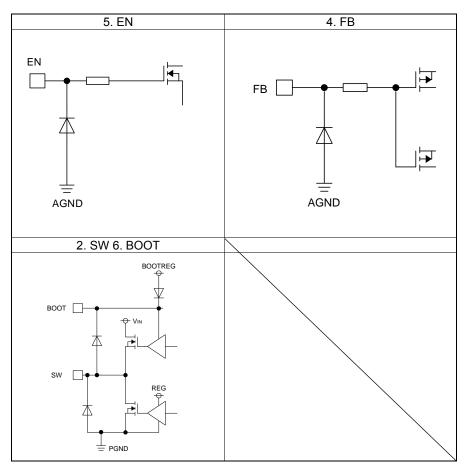


Inner 2 Layer

Bottom Layer

Figure 62. Example of PCB Layout

# I/O Equivalence Circuits



## **Operational Notes**

## 1. Reverse Connection of Power Supply

Connecting the power supply in reverse polarity can damage the IC. Take precautions against reverse polarity when connecting the power supply, such as mounting an external diode between the power supply and the IC's power supply pins.

## 2. Power Supply Lines

Design the PCB layout pattern to provide low impedance supply lines. Furthermore, connect a capacitor to ground at all power supply pins. Consider the effect of temperature and aging on the capacitance value when using electrolytic capacitors.

## 3. Ground Voltage

Ensure that no pins are at a voltage below that of the ground pin at any time, even during transient condition. However, pins that drive inductive loads (e.g. motor driver outputs, DC-DC converter outputs) may inevitably go below ground due to back EMF or electromotive force. In such cases, the user should make sure that such voltages going below ground will not cause the IC and the system to malfunction by examining carefully all relevant factors and conditions such as motor characteristics, supply voltage, operating frequency and PCB wiring to name a few.

## 4. Ground Wiring Pattern

When using both small-signal and large-current ground traces, the two ground traces should be routed separately but connected to a single ground at the reference point of the application board to avoid fluctuations in the small-signal ground caused by large currents. Also ensure that the ground traces of external components do not cause variations on the ground voltage. The ground lines must be as short and thick as possible to reduce line impedance.

## 5. Recommended Operating Conditions

The function and operation of the IC are guaranteed within the range specified by the recommended operating conditions. The characteristic values are guaranteed only under the conditions of each item specified by the electrical characteristics.

## 6. Inrush Current

When power is first supplied to the IC, it is possible that the internal logic may be unstable and inrush current may flow instantaneously due to the internal powering sequence and delays, especially if the IC has more than one power supply. Therefore, give special consideration to power coupling capacitance, power wiring, width of ground wiring, and routing of connections.

#### 7. Testing on Application Boards

When testing the IC on an application board, connecting a capacitor directly to a low-impedance output pin may subject the IC to stress. Always discharge capacitors completely after each process or step. The IC's power supply should always be turned off completely before connecting or removing it from the test setup during the inspection process. To prevent damage from static discharge, ground the IC during assembly and use similar precautions during transport and storage.

## 8. Inter-pin Short and Mounting Errors

Ensure that the direction and position are correct when mounting the IC on the PCB. Incorrect mounting may result in damaging the IC. Avoid nearby pins being shorted to each other especially to ground, power supply and output pin. Inter-pin shorts could be due to many reasons such as metal particles, water droplets (in very humid environment) and unintentional solder bridge deposited in between pins during assembly to name a few.

#### 9. Unused Input Pins

Input pins of an IC are often connected to the gate of a MOS transistor. The gate has extremely high impedance and extremely low capacitance. If left unconnected, the electric field from the outside can easily charge it. The small charge acquired in this way is enough to produce a significant effect on the conduction through the transistor and cause unexpected operation of the IC. So unless otherwise specified, unused input pins should be connected to the power supply or ground line.

## **Operational Notes – continued**

#### 10. Regarding the Input Pin of the IC

This monolithic IC contains P+ isolation and P substrate layers between adjacent elements in order to keep them isolated. P-N junctions are formed at the intersection of the P layers with the N layers of other elements, creating a parasitic diode or transistor. For example (refer to figure below):

When GND > Pin A and GND > Pin B, the P-N junction operates as a parasitic diode. When GND > Pin B, the P-N junction operates as a parasitic transistor.

Parasitic diodes inevitably occur in the structure of the IC. The operation of parasitic diodes can result in mutual interference among circuits, operational faults, or physical damage. Therefore, conditions that cause these diodes to operate, such as applying a voltage lower than the GND voltage to an input pin (and thus to the P substrate) should be avoided.

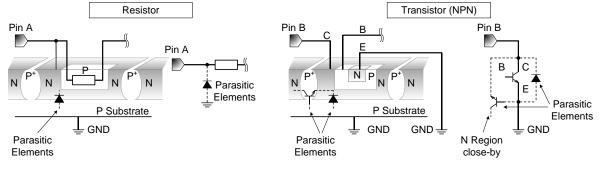


Figure 63. Example of Monolithic IC Structure

#### 11. Ceramic Capacitor

When using a ceramic capacitor, determine a capacitance value considering the change of capacitance with temperature and the decrease in nominal capacitance due to DC bias and others.

#### 12. Thermal Shutdown Circuit (TSD)

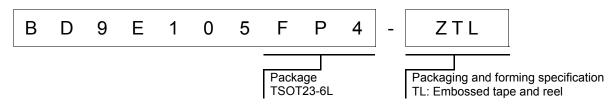
This IC has a built-in thermal shutdown circuit that prevents heat damage to the IC. Normal operation should always be within the IC's maximum junction temperature rating. If however the rating is exceeded for a continued period, the junction temperature (Tj) will rise which will activate the TSD circuit that will turn OFF power output pins. When the Tj falls below the TSD threshold, the circuits are automatically restored to normal operation.

Note that the TSD circuit operates in a situation that exceeds the absolute maximum ratings and therefore, under no circumstances, should the TSD circuit be used in a set design or for any purpose other than protecting the IC from heat damage.

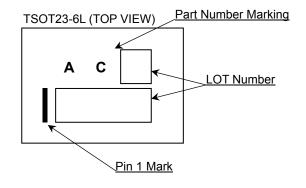
#### 13. Over Current Protection Circuit (OCP)

This IC incorporates an integrated overcurrent protection circuit that is activated when the load is shorted. This protection circuit is effective in preventing damage due to sudden and unexpected incidents. However, the IC should not be used in applications characterized by continuous operation or transitioning of the protection circuit.

## **Ordering Information**



## **Marking Diagram**



# Datasheet

## **Physical Dimension and Packing Information** TSOT23-6L Package Name $2. 9\pm0. 2$ $4^{\circ} + 6^{\circ}_{-4^{\circ}}$ 0 $8\pm0.$ $6\pm 0$ . $4\pm0$ . 3 ÷ 0. $0.\ 1\ 6\pm 0.\ 0\ 5$ 1PIN MARK S $8\pm 0.05$ 0. 95 MAX 0. 05 0. $44^{+0.06}_{-0.14}$ 0.95 $0.5 \pm 0.$ 0. □ 0. 1 S (UNIT:mm) PKG: TSOT23-6L Drawing No. EX001-0114 < Tape and Reel Information > Tape Embossed carrier tape 3500pcs Quantity Direction of feed ΤL The direction is the pin 1 of product is at the lower left when you hold reel on the left hand and you pull out the tape on the right hand Ο 0 0 Ο Ο Ο Ο Ο Ο 0 Ο Ο

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E2 TR

TL E1

E2 TR

TL E1

Reel

E2 TR

Pocket Quadrants

TL E1

E2 TR

TL E1

E2 TR

TL E1

E2 TR

TL E1

Direction of feed

## **Revision History**

| Date        | Revision | Changes     |
|-------------|----------|-------------|
| 21.May.2021 | 001      | New Release |

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|---|
|---|

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| CLASSⅣ | CLASSII | CLASSⅢ     | CLASSI |

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